Jun'ichi Kanasaki

List of Publications by Year
in descending order

33	547	687363 13	642732 23
papers	citations	h-index	g-index

33	33	33	597
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Ultrafast relaxation of photoinjected nonthermal electrons in the Î“ valley of GaAs studied by time- and angle-resolved photoemission spectroscopy. Physical Review B, 2021, 104, .	3.2	8
2	Ultrafast relaxation dynamics of highly excited hot electrons in silicon. Physical Review B, 2019, 100, .	3.2	13
3	Energy relaxation mechanism of hot-electron ensembles in GaAs: Theoretical and experimental study of its temperature dependence. Physical Review B, 2018, 97, .	3.2	16
4	Ultrafast dynamics in photoexcited valence-band states of Si studied by time- and angle-resolved photoemission spectroscopy of bulk direct transitions. Physical Review B, 2018, 97, .	3.2	6
5	Electronic structure of the surface unoccupied band of Ge(001)- <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>c</mml:mi><mml:mo>(</mml:mo><mml:mn>4</mml:mn><mml:mn>2</mml:mn> : Direct imaging of surface electron relaxation pathways. Physical Review B, 2017, 96, .	3.2	4
6	Comparison of Electronic-Excitation-Induced Structural Modification of Carbon-Based Nanomaterials with that of Semiconductor Surfaces. Nano, 2016, 11, 1630001.	1.0	2
7	Formation of hot-electron ensembles quasiequilibrated in momentum space by ultrafast momentum scattering of highly excited hot electrons photoinjected into the Î“ valley of GaAs. Physical Review B, 2016, 93, .	3.2	37
8	Ultrafast scattering processes of hot electrons in InSb studied by time- and angle-resolved photoemission spectroscopy. Physical Review B, 2015, 91, .	3.2	25
9	Imaging Energy-, Momentum-, and Time-Resolved Distributions of Photoinjected Hot Electrons in GaAs. Physical Review Letters, 2014, 113, 237401.	7.8	37
10	Crucial roles of holes in electronic bond rupture on semiconductor surfaces. Surface Science, 2014, 626, 49-52.	1.9	1
11	Role of applied bias and tip electronic structure in the scanning tunneling microscopy imaging of highly oriented pyrolytic graphite. Physical Review B, 2012, 85, .	3.2	18
12	Ultrafast relaxation of highly excited hot electrons in Si: Roles of the<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi mathvariant="normal">L</mml:mi><mml:mo>â^'</mml:mo><mml:mi mathvariant="normal">X</mml:mi></mml:mrow></mml:math>intervalley scattering. Physical Review B, 2011, 84, .	3.2	38
13	Intact-sheet double-layer ablation induced by femtosecond-laser excitation of graphite. Surface Science, 2011, 605, 1497-1502.	1.9	4
14	Formation of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>s</mml:mi><mml:msup><mml:mi>p</mml:mi><mml:mn>3</mml:mn></mml:msup></mml:math>-Bonded Carbon Nanostructures by Femtosecond Laser Excitation of Graphite. Physical Review Letters, 2009, 102, 087402.	7.8	132
15	Fermi-level dependent morphology in photoinduced bond breaking on (110) surfaces of IIIâ€“V semiconductors. Surface Science, 2007, 601, 2367-2372.	1.9	9
16	Two-hole localization mechanism for electronic bond rupture of surface atoms by laser-induced valence excitation of semiconductors. Physical Review B, 2006, 74, .	3.2	11
17	Photoinduced Structural Instability of the InP(110)â^'(1Ã—1)Surface. Physical Review Letters, 2004, 93, 117401.	7.8	17
18	Electronic bond rupture of Si atoms on Si()-(2Ã—1) induced by 1.16-eV photon excitation. Surface Science, 2003, 528, 115-120.	1.9	3

#	Article	IF	Citations
19	Laser-induced electronic desorption of Si atoms fromSi(111)â^'(7Ã—7). Physical Review B, 2002, 66, .	3.2	13
20	Primary Processes of Laser-Induced Selective Dimer-Layer Removal onSi(001)â^'(2Ã—1). Physical Review Letters, 2002, 89, 257601.	7.8	37
21	<title>Laser-induced electronic desorption and structural changes on Si(001)-(2x1)</title>. , 2002, , .		1
22	Laser-induced electronic desorption from InP surfaces studied by femtosecond nonresonant ionization spectroscopy. Physical Review B, 2001, 64, .	3.2	16
23	<title>Laser-induced electronic bond breaking and structural changes on semiconductor surfaces</title>. , 1999, , .		3
24	Laser-induced bond breaking and structural changes on Si(111)-7Ã—7 surfaces. Applied Surface Science, 1998, 127-129, 33-39.	6.1	1
25	Low energy laser photoelectron study of defect states on cleaved Si(111)2 Ã— 1 surfaces. Surface Science, 1996, 349, L107-L110.	1.9	3
26	Laser-induced bond breaking of the adatoms of the Si(111)-7 Ã— 7 surface. Surface Science, 1996, 349, L153-L158.	1.9	25
27	Site-sensitive yield of atomic emission induced by laser irradiation on Si(111)â^'7Ã—7 surface. Solid State Communications, 1996, 98, 913-916.	1.9	22
28	Photon energy dependence of the laser-induced emission yield of Si atoms from the Si(100) surface. Journal of Physics Condensed Matter, 1996, 8, 1475-1484.	1.8	3
29	The DIET from semiconductor surfaces by excitation of valence electrons. Nuclear Instruments & Methods in Physics Research B, 1995, 101, 93-102.	1.4	7
30	Enhancement of Emission of Si Atoms from Si(100) Surface by Low-Rate Br Exposure: A New Model of Dry Etching Based on Defect-Adsorbate Interaction. Japanese Journal of Applied Physics, 1994, 33, 2255-2257.	1.5	1
31	Defect-initiated atomic emissions from semiconductor surfaces induced by laser irradiation: electronic cleaning of defects on surfaces. Applied Surface Science, 1994, 79-80, 100-103.	6.1	6
32	Defect initiated particle emission from semiconductor surfaces by laser irradiation. Surface Science, 1993, 283, 169-176.	1.9	11
33	Laser-Induced Electronic Emissions of Si Atoms from Si(100) Surfaces. Japanese Journal of Applied Physics, 1993, 32, L859-L862.	1.5	19